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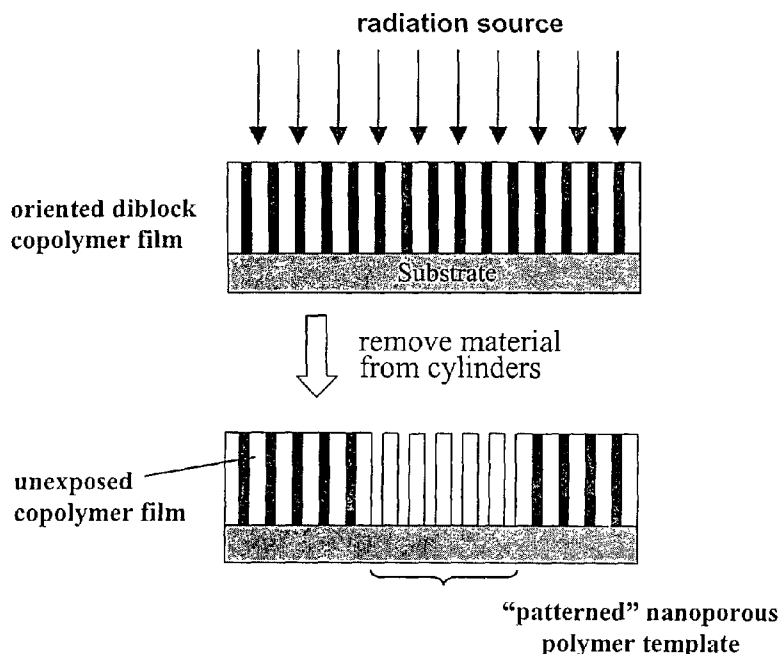
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- (71) Applicant (for all designated States except US): **UNIVERSITY OF MASSACHUSETTS** [US/US]; One Beacon Street, 26th Floor, Boston, MA 02108 (US).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **TOUMINEN, Mark, T.** [US/US]; 54 Montague Road, Shutesbury, MA 01072 (US). **RUSSELL, Thomas, P.** [US/US]; 496 South East Street, Amherst, MA 01002 (US). **URSACHE, Andrei** [RO/US]; 280 Sunset Avenue, Pince Hall, 308, Amherst, MA 01003 (US). **BAL, Mustafa** [TR/US]; 990 North Pleasant Street, Northvillage Apt. F-11, Amherst, MA 01002 (US).
- (74) Agent: **FASSE, Peter, J.**; Fish & Richardson P.C., 225 Franklin Street, Boston, MA 02110-2804 (US).
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(57) Abstract: Pathways to rapid and reliable fabrication of three-dimensional nanostructures are provided. Simple methods are described for the production of well-ordered, multilevel nanostructures. This is accomplished by patterning block copolymer templates with selective exposure to a radiation source. The resulting multi-scale lithographic template can be treated with post-fabrication steps to produce multilevel, three-dimensional, integrated nanoscale media, devices, and systems.



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